AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of forming a liquid crystal display (LCD) panel comprising:

forming a thin film transistor and a pixel electrode on a first substrate;

forming a dielectric frame having a first height and a sealant structure having a second height on a second substrate, the dielectric frame including a material having a small dielectric constant, the material including photoacrylate;

dispensing a plurality of droplets of liquid crystal on the first substrate formed no dielectric frame so that the plurality of droplets of liquid crystal on the first substrate are spaced with each other;

attaching the first and second substrates to each other for forming the LCD panel, wherein a primary cell gap of the LCD panel is formed under vacuum state and then is exposed to atmospheric pressure, so that a secondary cell gap of the LCD panel is formed by the amount of the liquid crystal and the pressure difference between the interior of the LCD panel and the atmosphere; and

completely hardening the sealant structure by exposure to UV ray under the atmospheric pressure [[no pressure]],

wherein the second height of the sealant structure is higher than the first height of the dielectric frame, a height difference between the first height and the second height is more than 1μm so that the height difference between the sealant structure and dielectric frame prevent the generation of bubble in liquid crystal, allows the dispensed liquid crystal to be uniformly distributed and not to hinder the dispensed liquid crystal from being moved and uniformly distributed between the first substrate and the second substrate,

wherein the first height the dielectric frame is a range of 1-2 μm and the second height of the sealant structure is in a range of 5-8 μm, and

wherein the second height of the sealant structure is proportional to the first height of the dielectric frame.

2. (Canceled).

3. (Canceled).

4. (Original) The method of claim 1, further comprising forming an electric field inducing window in the pixel electrode.

5. (Previously Amended) The method of claim 4, wherein the electric field inducing window has a slit shape.

6. (Withdrawn) The method of claim 1, wherein forming the thin film transistor includes:

forming a gate electrode on the first substrate;
forming a gate insulating film on the first substrate;
forming a semiconductor layer on the gate insulating film; and
forming source and drain electrodes on the semiconductor layer.

7. (Previously Presented) The method of claim 1, wherein the thin film transistor is formed to have an L-shaped channel.

8. (Withdrawn) The method of claim 1, wherein the thin film transistor is formed to have a U-shape.

9. (Original) The method of claim 1, wherein the dielectric frame drives the liquid crystal in various directions.

10-11. (Canceled).

12. (Original) The method of claim 1, further comprising forming a common electrode on the second substrate.

13. (Original) The method of claim 12, wherein the dielectric frame is formed on the common electrode.

14. (Original) The method of claim 1, further comprising forming an alignment layer on at least one of the first and second substrates.

15. (Original) The method of claim 14, wherein the alignment layer is selected from the group consisting of polyimide, polyamide, polyvinyl alcohol, polyamic acid, and silicon oxide.

16. (Withdrawn) The method of claim 14, wherein the alignment layer is selected from the group consisting of polyvinylcinnamate, polysiloxanecinnamate, and cellulosecinnamate.

17. (Original) The method of claim 1, further comprising forming a phase difference film on at least one of the first and second substrates.

18. (Original) The method of claim 17, wherein the phase difference film includes a negative uniaxial film.

19. (Previously Presented) The method of claim 17, wherein the phase difference film includes a negative biaxial film.

20. (Canceled).

21. (Withdrawn) The method of claim 1, wherein the first height is a range of 1-2 μm and the second height is about 4 μm.

22. (Withdrawn) The method of claim 1, wherein the first height is a range of 1-1.5 μm and the second height is about 3 μm.

23. (Withdrawn) The method of claim 1, wherein the first height is about 1 μm and the second height is about 2 μm.

24. (Withdrawn) A method of forming a liquid crystal display device comprising:
forming a gate electrode on a first substrate;
forming a gate insulating film on the gate electrode and the first substrate;

forming a semiconductor layer on the gate insulating film;

forming source and drain electrodes on the semiconductor layer;

forming a pixel electrode contacting the drain electrode, the pixel electrode including an electric field inducing window;

forming a dielectric frame having a first height and a sealant having a second height on a second substrate, the first height of the dielectric frame being different from the second height of the sealant, the dielectric frame capable of causing an electric field distortion;

dispensing liquid crystal on the first substrate; and

attaching the first and second substrates to each other.

25. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-2 μm and the second height is in a range of 5-8 μm.

26. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-2 μm and the second height is about 4 μm.

27. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-1.5 μm and the second height is about 3 μm.

28. (Withdrawn) The method of claim 24, wherein the first height is about 1 μm and the second height is about 2 μm.

29. (Canceled).